

# MAZTxxxHG Series

## Silicon planar type

For surge absorption circuit

### ■ Features

- Two elements anode-common type
- Power dissipation  $P_D$  : 150 mW

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

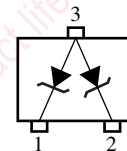
Parameter	Symbol	Rating	Unit
Power dissipation *	$P_D$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \*:  $P_D = 150$  mW achieved with a printed circuit board.

### ■ Package

- Code  
SSMini3-F3
- Pin Name  
1: Cathode 1  
2: Cathode 2  
3: Anode

### ■ Internal Connection



### ■ Common Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Zener voltage*	$V_Z$	$I_Z$ Specified value				V
Zener rise operating resistance	$R_{ZK}$	$I_Z$ Specified value				$\Omega$
Zener operating resistance	$R_Z$	$I_Z$ Specified value				$\Omega$
Reverse current	$I_R$	$V_R$ Specified value				$\mu\text{A}$

Refer to the list of the electrical characteristics within part numbers

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. Electrostatic breakdown voltage:  $\pm 10$  kV

Test method: IEC1000-4-2 (C = 150 pF, R = 330  $\Omega$ , Contact discharge: 10 times)

3. \*: The temperature must be controlled  $25^\circ\text{C}$  for  $V_Z$  measurement.

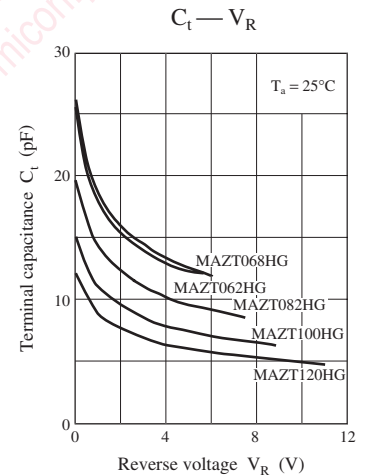
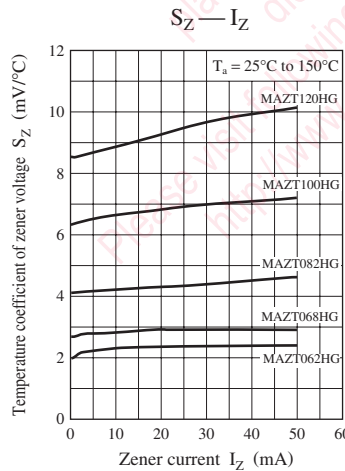
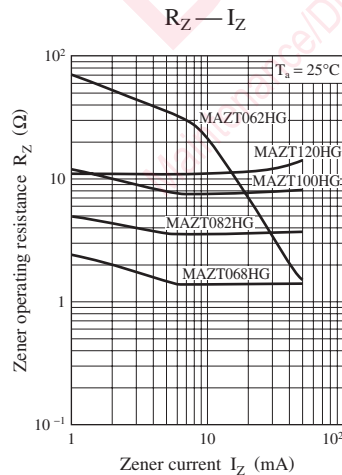
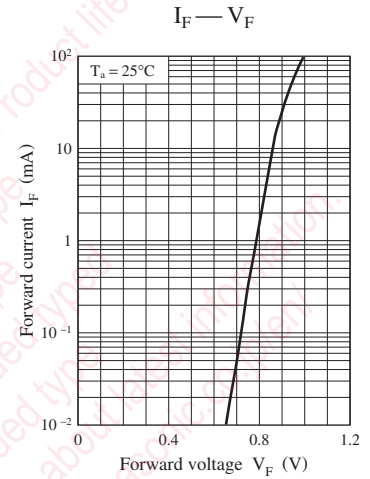
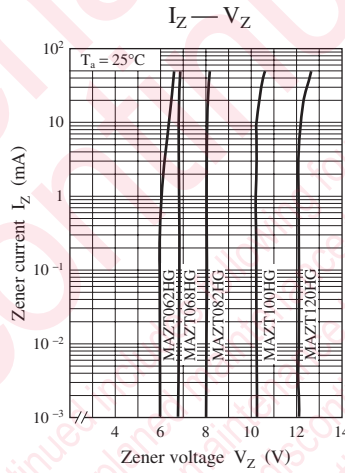
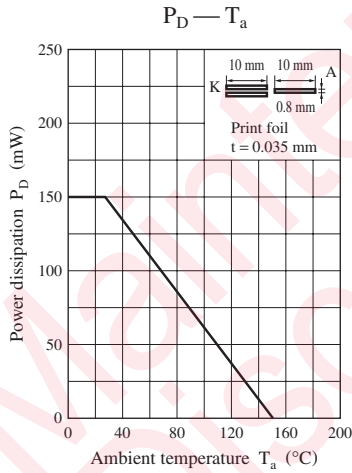
$V_Z$  value measured at other temperature must be adjusted to  $V_Z (25^\circ\text{C})$

$V_Z$  guaranteed 20 ms after current flow.

■ Electrical characteristics within part numbers  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

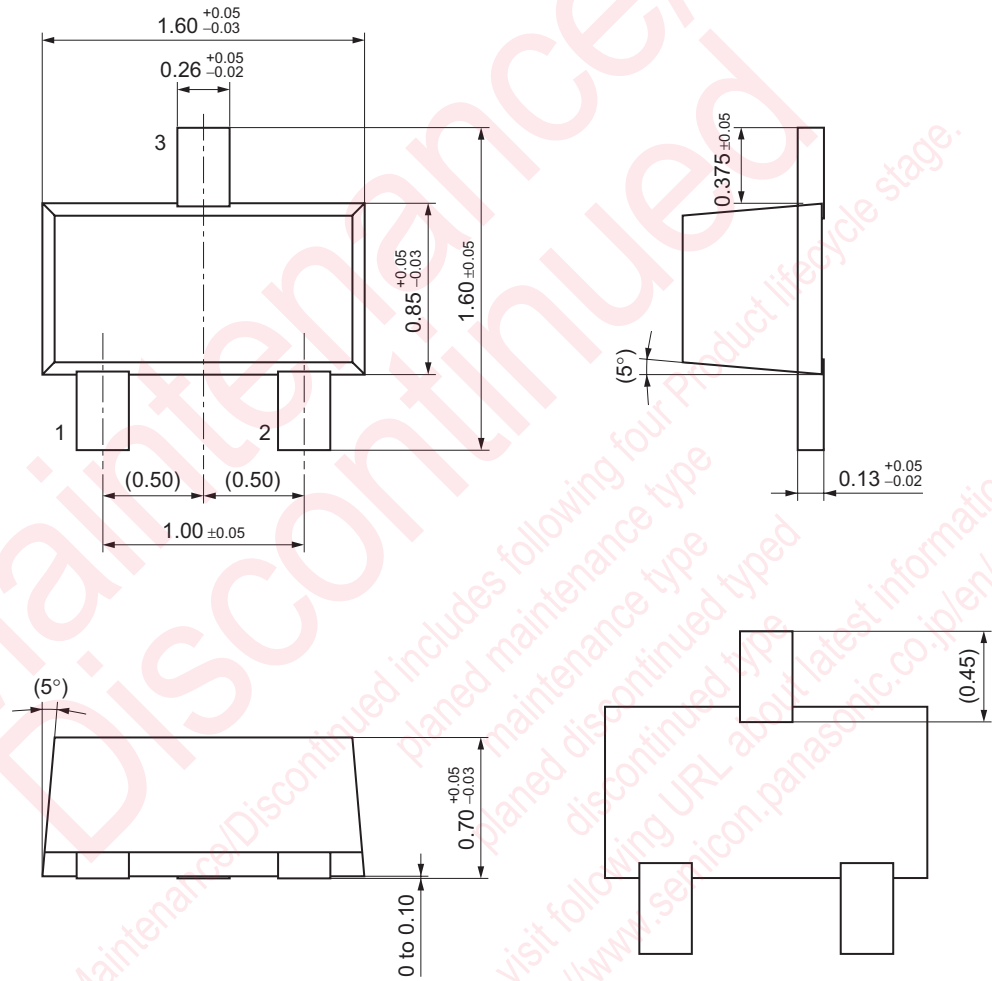
Part number	Zener voltage				Reverse current		Zener operating resistance	Zener rise operating resistance	Marking symbol
	$V_Z$ (V)			$I_Z$ (mA)	$I_R$ (mA)	$V_R$ (V)	$R_Z$ ( $\Omega$ )	$R_{ZK}$ ( $\Omega$ )	
	Min	Nom	Max				$I_Z = 5\text{ mA}$	$I_Z = 0.5\text{ mA}$	
MAZT062HG	5.8	6.2	6.6	5	0.2	4	50	100	6.2Z
MAZT068HG	6.4	6.8	7.2	5	0.1	4	30	60	6.8Z
MAZT082HG	7.7	8.2	8.7	5	0.1	5	30	60	8.2Z
MAZT100HG	9.4	10.0	10.6	5	0.05	7	30	60	10Z
MAZT120HG	11.4	12.0	12.7	5	0.05	9	30	80	12Z

Note) \*:  $I_Z = 1.0\text{ mA}$



SSMini3-F3

Unit: mm



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